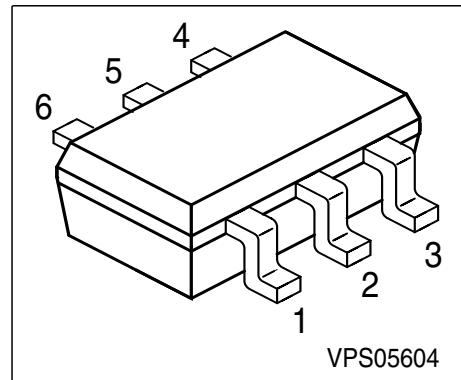
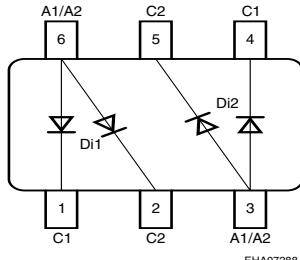


## Silicon Switching Diode Array

- For high-speed switching applications
- Common anode
- Internal (galvanic) isolated diode arrays in one package



| Type    | Marking | Pin Configuration |      |        |      |      |        | Package |
|---------|---------|-------------------|------|--------|------|------|--------|---------|
| BAW 56S | A1s     | 1=C1              | 2=C2 | 3=A1/2 | 4=C1 | 5=C2 | 6=A1/2 | SOT-363 |

### Maximum Ratings

| Parameter   | Symbol    | Value       | Unit             |
|---|-----------|-------------|------------------|
| Diode reverse voltage                             | $V_R$     | 70          | V                |
| Peak reverse voltage                              | $V_{RM}$  | 70          |                  |
| Forward current                                   | $I_F$     | 200         | mA               |
| Surge forward current, $t = 1 \mu\text{s}$        | $I_{FS}$  | 4.5         | A                |
| Total power dissipation, $T_S = 85^\circ\text{C}$ | $P_{tot}$ | 250         | mW               |
| Junction temperature                              | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                               | $T_{stg}$ | -65 ... 150 |                  |

### Thermal Resistance

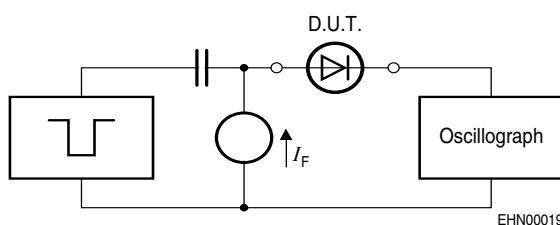
|                            |            |            |     |
|----------------------------|------------|------------|-----|
| Junction - ambient 1)      | $R_{thJA}$ | $\leq 530$ | K/W |
| Junction - soldering point | $R_{thJS}$ | $\leq 260$ |     |

1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 0.5cm<sup>2</sup> Cu

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

| Parameter   | Symbol            | Values |      |      | Unit          |
|---|-------------------|--------|------|------|---------------|
|   |                   | min.   | typ. | max. |               |
| <b>DC characteristics</b>   |                   |        |      |      |               |
| Breakdown voltage<br>$I_{(\text{BR})} = 100 \mu\text{A}$  | $V_{(\text{BR})}$ | 70     | -    | -    | V             |
| Forward voltage<br>$I_F = 1 \text{ mA}$   | $V_F$             | -      | -    | 715  | mV            |
| $I_F = 10 \text{ mA}$   |                   | -      | -    | 855  |               |
| $I_F = 50 \text{ mA}$   |                   | -      | -    | 1000 |               |
| $I_F = 150 \text{ mA}$  |                   | -      | -    | 1250 |               |
| Reverse current<br>$V_R = 70 \text{ V}$   | $I_R$             | -      | -    | 2.5  | $\mu\text{A}$ |
| Reverse current<br>$V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$  | $I_R$             | -      | -    | 30   |               |
| $V_R = 70 \text{ V}, T_A = 150^\circ\text{C}$   |                   | -      | -    | 50   |               |
| <b>AC characteristics</b>   |                   |        |      |      |               |
| Diode capacitance<br>$V_R = 0 \text{ V}, f = 1 \text{ MHz}$   | $C_D$             | -      | -    | 1.5  | pF            |
| Reverse recovery time<br>$I_F = 10 \text{ mA}, I_R = 10 \text{ mA}, R_L = 100 \Omega$ ,<br>measured at $I_R = 1 \text{ mA}$ | $t_{rr}$          | -      | -    | 6    | ns            |

### Test circuit for reverse recovery time

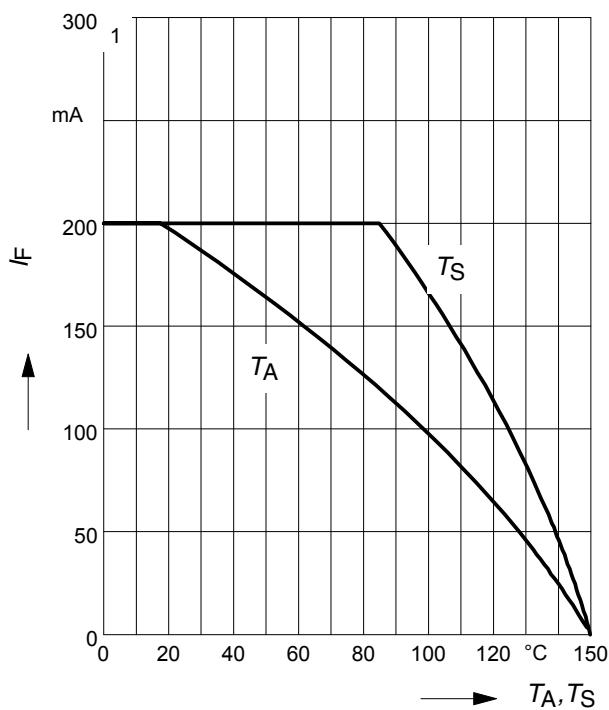


Pulse generator:  $t_p = 100\text{ns}$ ,  $D = 0.05$ ,  
 $t_r = 0.6\text{ns}$ ,  $R_i = 50\Omega$

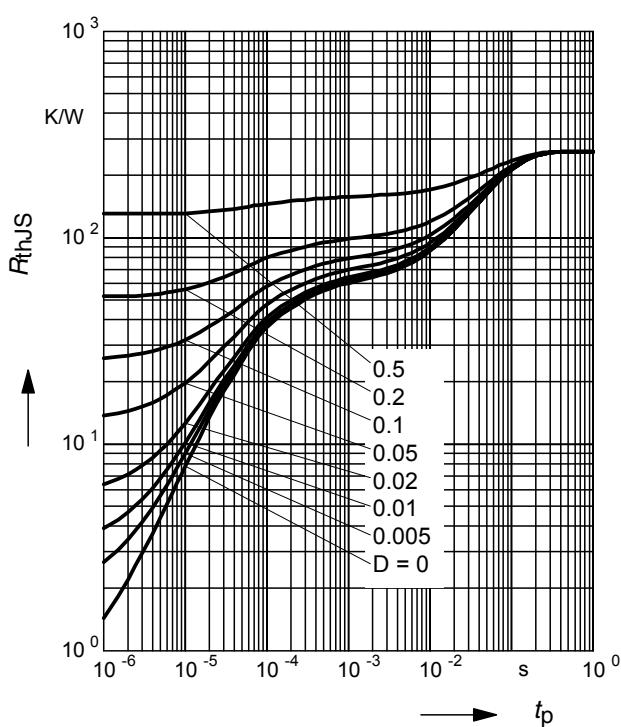
Oscillograph:  $R = 50\Omega$ ,  $t_r = 0.35\text{ns}$ ,  
 $C \leq 1\text{pF}$

**Forward current  $I_F = f(T_A^*; T_S)$**

\* Package mounted on epoxy

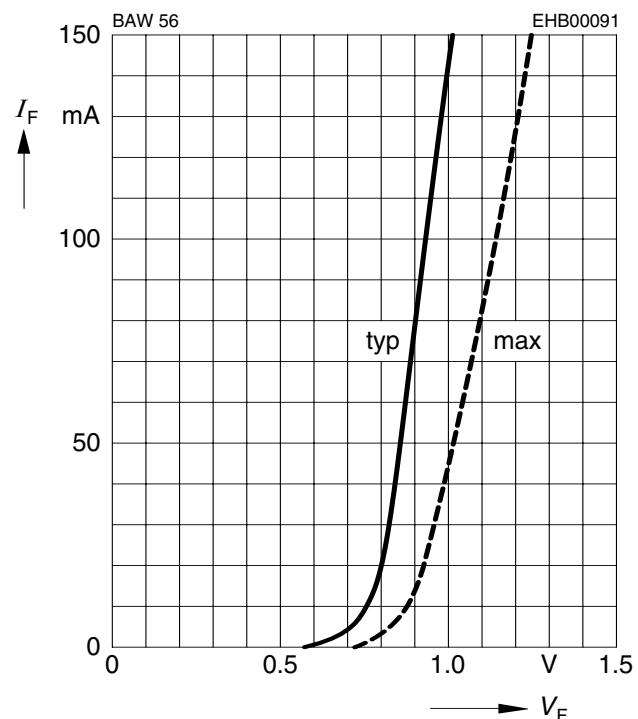


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



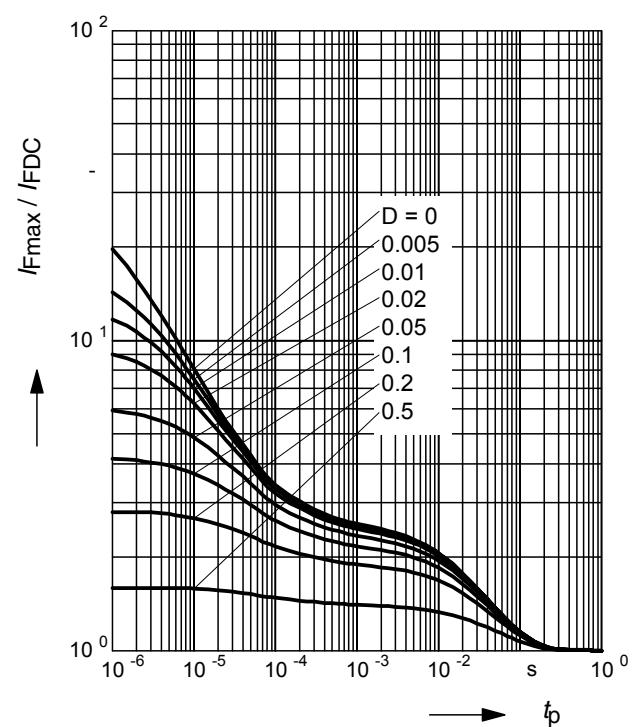
**Forward current  $I_F = f(V_F)$**

$T_A = 25^\circ\text{C}$

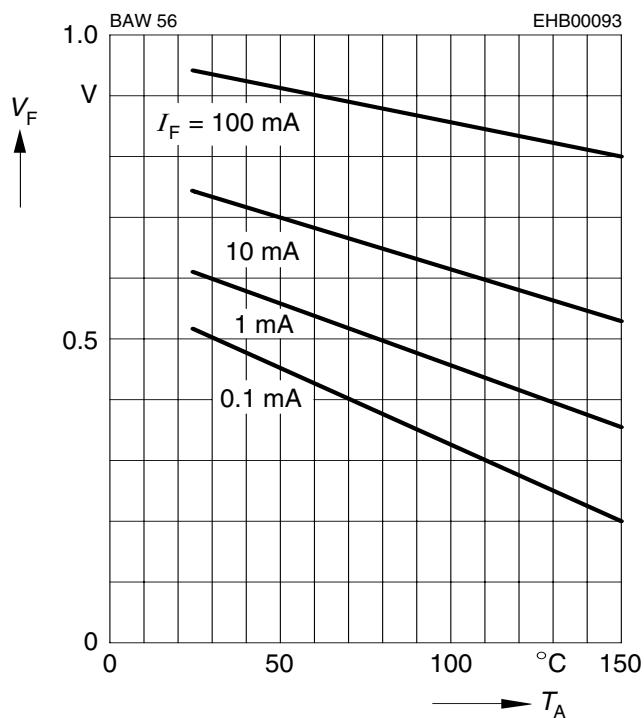


**Permissible Pulse Load**

$I_{Fmax} / I_{FDC} = f(t_p)$



**Forward voltage  $V_F = f(T_A)$**



**Reverse current  $I_R = f(T_A)$**

